### Silicon NPN Triple Diffused

# HITACHI

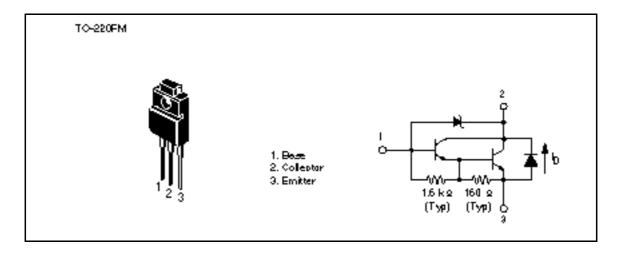
#### **Application**

High voltage switching, igniter

#### **Features**

- Built-in High voltage zener diode (300 V)
- · High speed switching

#### **Outline**





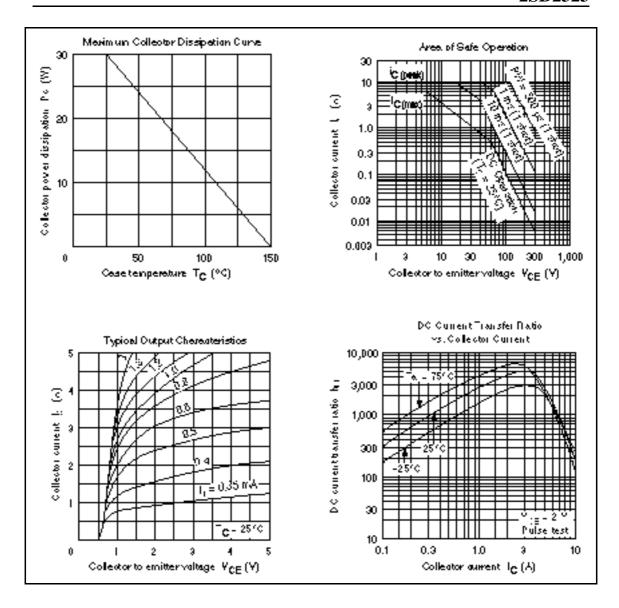
### Absolute Maximum Ratings ( $Ta = 25^{\circ}C$ )

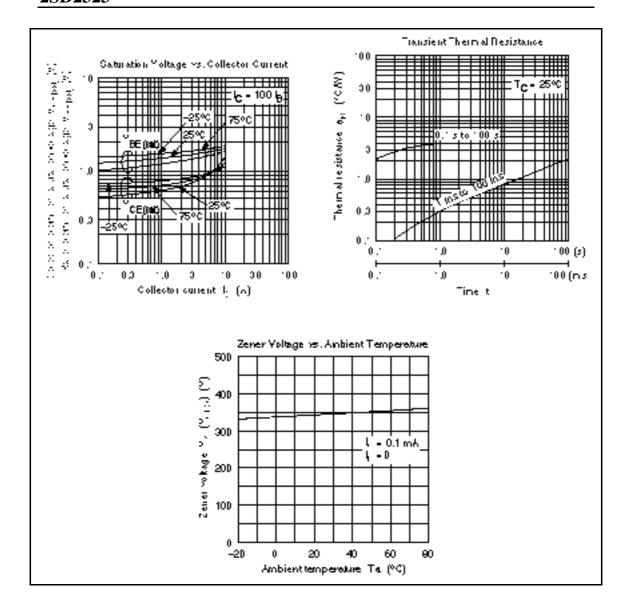
Item	Symbol	Rating	Unit
Collector to base voltage	$V_{\text{CBO}}$	300	V
Collector to emitter voltage	V <sub>CEO</sub>	300	V
Emitter to base voltage	$V_{EBO}$	7	V
Collector current	I <sub>c</sub>	6	А
Diode current	I <sub>D</sub> *1	6	А
Collector peak current	I <sub>C(peak)</sub>	10	A
Collector power dissipation	P <sub>c</sub> *1	30	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. Value at  $T_c = 25$ °C.

### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	300	_	420	V	$I_{\rm C} = 0.1 \text{ mA}, I_{\rm E} = 0$
Collector to emitter sustain voltage	$V_{\text{CEO(SUS)}}$	300	_	_	V	$I_{C} = 3 \text{ A}, R_{BE} = , L = 10 \text{ mH}$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	_	_	V	$I_{\rm E} = 50$ mA, $I_{\rm C} = 0$
Collector cutoff current	I <sub>CEO</sub>		_	100	μΑ	$V_{CE} = 300 \text{ V}, R_{BE} =$
DC current transfer ratio	h <sub>FE</sub>	500	_	_		$V_{CE} = 2 \text{ V}, I_{C} = 4 \text{ A}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	1.5	V	$I_C = 4 \text{ A}, I_B = 40 \text{ mA}$
Base to emitter saturation voltage	$V_{BE(sat)}$	_	_	2.0	V	$I_C = 4 \text{ A}, I_B = 40 \text{ mA}$
Emitter to collector forward voltage	V <sub>ECF</sub>	_	_	3.5	V	I <sub>F</sub> = 6 A
Turn on time	t <sub>on</sub>	_	1.2	_	μs	$I_{c} = 4 \text{ A}, V_{cc} = 20 \text{ V}$
Storage time	$t_{stg}$	_	8.0	_		$I_{B1} = -I_{B2} = 40 \text{ mA}$
Fall time	t <sub>f</sub>		8.0			





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